NPN Silicon Epitaxial Planar Transistor

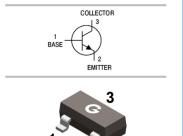
S9013

1

Features

- High collector current
- Complimentary to S9012
- Excellent h_{FE} linearity





SOT-23

Mechanical Data

Case: SOT-23

• Molding compound: UL flammability classification rating 94V-0

• Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
S9013	SOT-23	3000 pcs / Tape & Reel	J3

Maximum Ratings (@ TA = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	40	V
Collector-Emitter Breakdown Voltage	Vceo	25	V
Emitter-Base Breakdown Voltage	V _{EBO}	5	V
Collector Current (Continuous)	Ic	0.5	Α
Collector Current (Peak)	Ісм	1	Α
Power Dissipation	P_D	0.3	W
Junction Temperature Range	TJ	-55 ~ + 150	°C
Storage Temperature Range	Тѕтс	-55 ~ + 150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance Junction-to-Air *1	RθJA	-	-	220	°C/W
Thermal Resistance Junction-to-Case *1	Rejc	-	-	130	°C/W
Thermal Resistance Junction-to-Lead *1	R ₀ JL	-	-	140	°C/W

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper

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Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

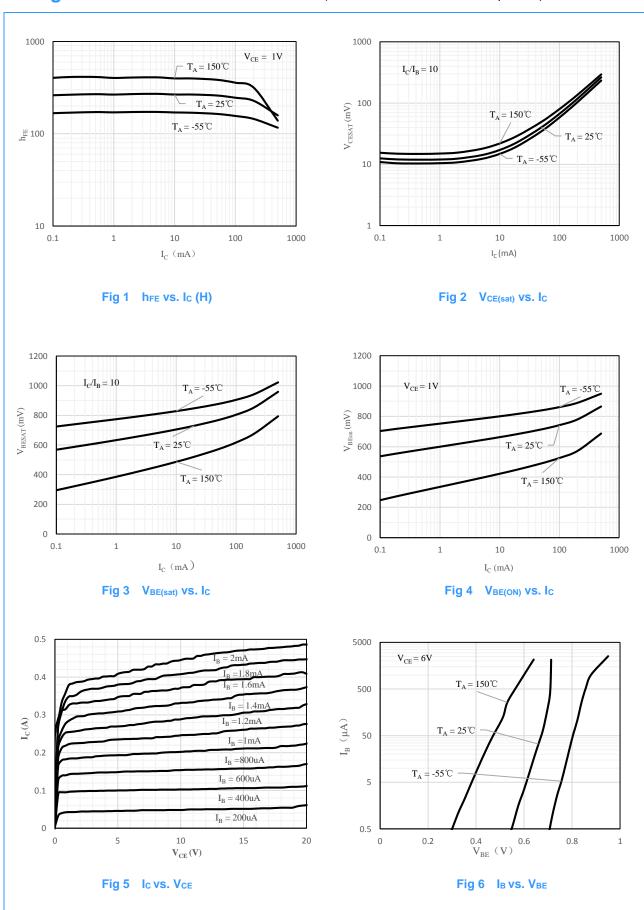
Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C = 100μA, I _E = 0	40	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = 0.1 \text{mA}, I_B = 0$	25	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = 100μA, I _C = 0	5	-	-	V
Collector Cut-off Current	Ісво	V _{CB} = 40V, I _E = 0	-	-	0.1	μΑ
Collector Cut-off Current	Iceo	V _{CE} = 20V, I _B = 0	-	-	0.1	μΑ
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _C = 0	-	-	0.1	μΑ
DC Comment Cain	h _{FE}	$V_{CE} = 1V$, $I_{C} = 50mA$	120	-	400	-
DC Current Gain		V _{CE} = 1V, I _C = 500mA	40	-	-	-
Collector-emitter Saturation Voltage	V _{CE(sat)}	I _C = 500mA, I _B = 50mA	-	-	0.6	V
Base-emitter Saturation Voltage	V _{BE(sat)}	Ic = 500mA, I _B = 50mA	-	-	1.2	V
Transition Frequency	f⊤	$I_C = 20$ mA, $V_{CE} = 6$ V, $f = 30$ MHZ	150	-	-	MHz

CLASSIFICATION OF hFE

Rank	L	Н	J
Range	120-200	200-350	300-400

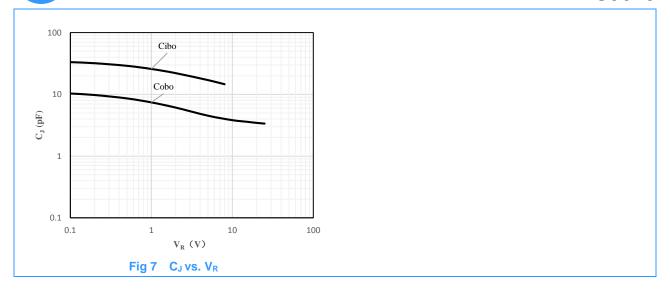


Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)



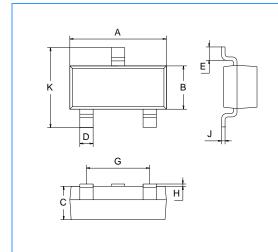
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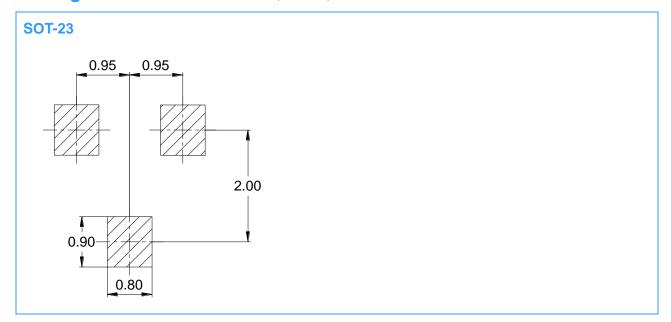


Package Outline Dimensions (Unit: mm)



SOT-23					
Dimension	Min.	Max.			
Α	2.70	3.10			
В	1.10	1.50			
С	0.90	1.10			
D	0.30	0.50			
E	0.35	0.48			
G	1.80	2.00			
Н	0.02	0.10			
J	0.05	0.15			
K	2.20	2.60			

Package Outline Dimensions (Unit: mm)



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